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Digital Transistors (BRT) R1 = 10 k Ω , R2 = 10 k Ω

NPN Transistors with Monolithic Bias Resistor Network

MUN2211, MMUN2211L, MUN5211, DTC114EE, DTC114EM3, NSBC114EF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

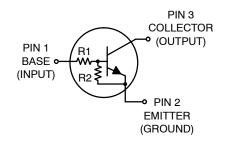
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25° C)

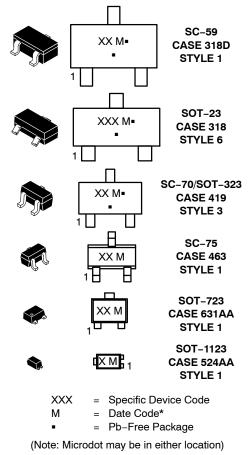
| Rating | Symbol | Max | Unit |
|--------------------------------|----------------------|-----|------|
| Collector-Base Voltage | V _{CBO} | 50 | Vdc |
| Collector-Emitter Voltage | V _{CEO} | 50 | Vdc |
| Collector Current – Continuous | ۱ _C | 100 | mAdc |
| Input Forward Voltage | V _{IN(fwd)} | 40 | Vdc |
| Input Reverse Voltage | V _{IN(rev)} | 10 | Vdc |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PIN CONNECTIONS



MARKING DIAGRAMS



*Date Code orientation may vary depending upon manufacturing location.

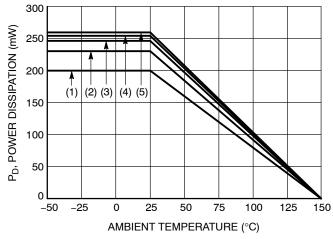
ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

| Table 1. | ORDERING INFORMATION |
|----------|----------------------|
| | |

| Device | Part Marking | Package | Shipping [†] |
|-----------------------------|--------------|----------------------------|-----------------------|
| MUN2211T1G, SMUN2211T1G | 8A | SC–59 (Pb–Free) | 3000 / Tape & Reel |
| MUN2211T3G, SMUN2211T3G | 8A | SC–59 (Pb–Free) | 10000 / Tape & Reel |
| MMUN2211LT1G, SMMUN2211LT1G | A8A | SOT-23 (Pb-Free) | 3000 / Tape & Reel |
| MMUN2211LT3G, SMMUN2211LT3G | A8A | SOT-23 (Pb-Free) | 10000 / Tape & Reel |
| MUN5211T1G, SMUN5211T1G | 8A | SC-70/SOT-323 (Pb-Free) | 3000 / Tape & Reel |
| SMUN5211T3G | 8A | SC-70/SOT-323 (Pb-Free) | 10000 / Tape & Reel |
| DTC114EET1G, SDTC114EET1G | 8A | SC–75 (Pb–Free) | 3000 / Tape & Reel |
| DTC114EM3T5G | 8A | SOT-723 (Pb-Free) | 8000 / Tape & Reel |
| NSBC114EF3T5G | A | SOT-1123 (Pb-Free) | 8000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.







(1) SC-75 and SC-70/SOT323; Minimum Pad

(4) SOT-1123; 100 mm², 1 oz. copper trace

(2) SC-59; Minimum Pad

(3) SOT-23; Minimum Pad

(5) SOT-723; Minimum Pad

Table 2. THERMAL CHARACTERISTICS

| | Characteristic | Symbol | Max | Unit |
|---|------------------------------|-----------------------------------|--------------------------|-------------|
| THERMAL CHARACTERISTIC | CS (SC–59) (MUN2211) | | | |
| Total Device Dissipation $T_A = 25^{\circ}C$ (Note 1) (Note 2) Derate above $25^{\circ}C$ | (Note 1) | PD | 230 338 1.8 | mW mW/°C |
| (Note 2) | | | 2.7 | |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | R _{θJA} | 540 370 | °C/W |
| Thermal Resistance, Junction to Lead (Note 2) | (Note 1) | $R_{	hetaJL}$ | 264 287 | °C/W |
| Junction and Storage Temper | ature Range | T _J , T _{stg} | –55 to +150 | °C |
| THERMAL CHARACTERISTIC | CS (SOT-23) (MMUN2211L) | | | |
| $\begin{array}{l} \mbox{Total Device Dissipation} \\ T_A = 25^\circ C \qquad (Note 1) \\ (Note 2) \\ \mbox{Derate above } 25^\circ C \\ (Note 2) \end{array}$ | (Note 1) | PD | 246 400 2.0 3.2 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | R _{θJA} | 508 311 | °C/W |
| Thermal Resistance, Junction to Lead (Note 2) | (Note 1) | $R_{	ext{	heta}JL}$ | 174 208 | °C/W |
| Junction and Storage Temper | ature Range | T _J , T _{stg} | –55 to +150 | °C |
| THERMAL CHARACTERISTIC | CS (SC-70/SOT-323) (MUN5211) | - | | |
| Total Device Dissipation T _A = 25°C (Note 1) (Note 2) | | P _D | 202 310 | mW |
| Derate above 25°C (Note 2) | (Note 1) | | 1.6 2.5 | mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{	hetaJA}$ | 618 403 | °C/W |
| Thermal Resistance, Junction to Lead (Note 2) | (Note 1) | $R_{	heta JL}$ | 280 332 | °C/W |
| Junction and Storage Temper | ature Range | T _J , T _{stg} | –55 to +150 | °C |
| THERMAL CHARACTERISTIC | CS (SC-75) (DTC114EE) | | | |
| Total Device Dissipation $T_A = 25^{\circ}C$ (Note 1) (Note 2) Derate above 25^{C} (Note 2) | (Note 1) | P _D | 200 300 1.6 2.4 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | $R_{	heta JA}$ | 600 400 | °C/W |
| Junction and Storage Temper | ature Range | T _J , T _{stg} | –55 to +150 | °C |
| THERMAL CHARACTERISTIC | CS (SOT-723) (DTC114EM3) | • | | |
| $\begin{array}{l} \mbox{Total Device Dissipation} \\ T_A = 25^\circ C \qquad (Note 1) \\ (Note 2) \\ \mbox{Derate above } 25^\circ C \\ (Note 2) \end{array}$ | (Note 1) | PD | 260 600 2.0 4.8 | mW mW/°C |
| Thermal Resistance, Junction to Ambient | (Note 1) (Note 2) | R _{θJA} | 480 205 | °C/W |
| Junction and Storage Temper | ature Range | T _J , T _{stg} | –55 to +150 | °C |
| 1. FR-4 @ Minimum Pad. | | • | | |

2. FR-4 @ 1.0 x 1.0 Inch Pad.

FR-4 @ 100 mm², 1 oz. copper traces, still air.
FR-4 @ 500 mm², 1 oz. copper traces, still air.



Table 2. THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit | | | | |
|---|---|--------------------------|-------------|--|--|--|--|
| THERMAL CHARACTERISTICS (SOT-1123) (NSBC114EF3) | THERMAL CHARACTERISTICS (SOT-1123) (NSBC114EF3) | | | | | | |
| $ \begin{array}{l} \mbox{Total Device Dissipation} \\ T_A = 25^\circ C & (Note 3) \\ (Note 4) \\ \mbox{Derate above } 25^\circ C & (Note 3) \\ (Note 4) \end{array} $ | PD | 254 297 2.0 2.4 | mW mW/°C | | | | |
| Thermal Resistance,(Note 3)Junction to Ambient(Note 4) | R _{θJA} | 493 421 | °C/W | | | | |
| Thermal Resistance, Junction to Lead (Note 3) | $R_{	extsf{	heta}JL}$ | 193 | °C/W | | | | |
| Junction and Storage Temperature Range | T _J , T _{stg} | –55 to +150 | °C | | | | |

1. FR-4 @ Minimum Pad.

2. FR-4 @ 1.0 x 1.0 lnch Pad. 3. FR-4 @ 100 mm², 1 oz. copper traces, still air. 4. FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T_A = 25° C, unless otherwise noted)

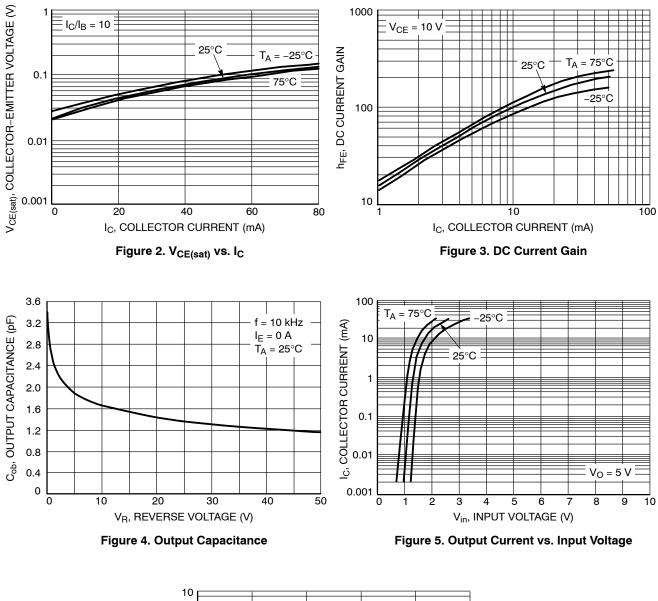
| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|--------------------------------|-----|-----|------|------|
| OFF CHARACTERISTICS | | | | | |
| Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$ | I _{CBO} | - | - | 100 | nAdc |
| Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$ | I _{CEO} | - | - | 500 | nAdc |
| Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0) | I _{EBO} | - | - | 0.5 | mAdc |
| Collector–Base Breakdown Voltage $(I_C = 10 \ \mu A, I_E = 0)$ | V _{(BR)CBO} | 50 | - | - | Vdc |
| Collector–Emitter Breakdown Voltage (Note 5) $(I_C = 2.0 \text{ mA}, I_B = 0)$ | V _{(BR)CEO} | 50 | - | - | Vdc |
| ON CHARACTERISTICS | • | • | | | |
| DC Current Gain (Note 5) $(I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V})$ | h _{FE} | 35 | 60 | - | |
| Collector–Emitter Saturation Voltage (Note 5) $(I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA})$ | V _{CE(sat)} | - | - | 0.25 | Vdc |
| Input Voltage (off) (V _{CE} = 5.0 V, I _C = 100 μA) | V _{i(off)} | - | 1.2 | 0.8 | Vdc |
| Input Voltage (on) (V _{CE} = 0.3 V, I _C = 10 mA) | V _{i(on)} | 2.5 | 1.8 | _ | Vdc |
| Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω) | V _{OL} | - | - | 0.2 | Vdc |
| Output Voltage (off) $(V_{CC} = 5.0 \text{ V}, \text{ V}_{B} = 0.5 \text{ V}, \text{ R}_{L} = 1.0 \text{ k}\Omega)$ | V _{OH} | 4.9 | - | - | Vdc |
| Input Resistor | R1 | 7.0 | 10 | 13 | kΩ |
| Resistor Ratio | R ₁ /R ₂ | 0.8 | 1.0 | 1.2 | |

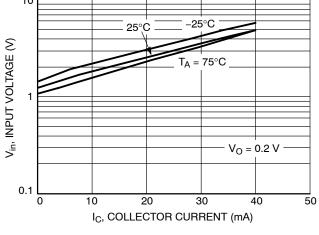
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

performance may not be indicated by the Electrical Characteristics if operated under different conditions. 5. Pulsed Condition: Pulse Width = 300 μ sec, Duty Cycle \leq 2%.



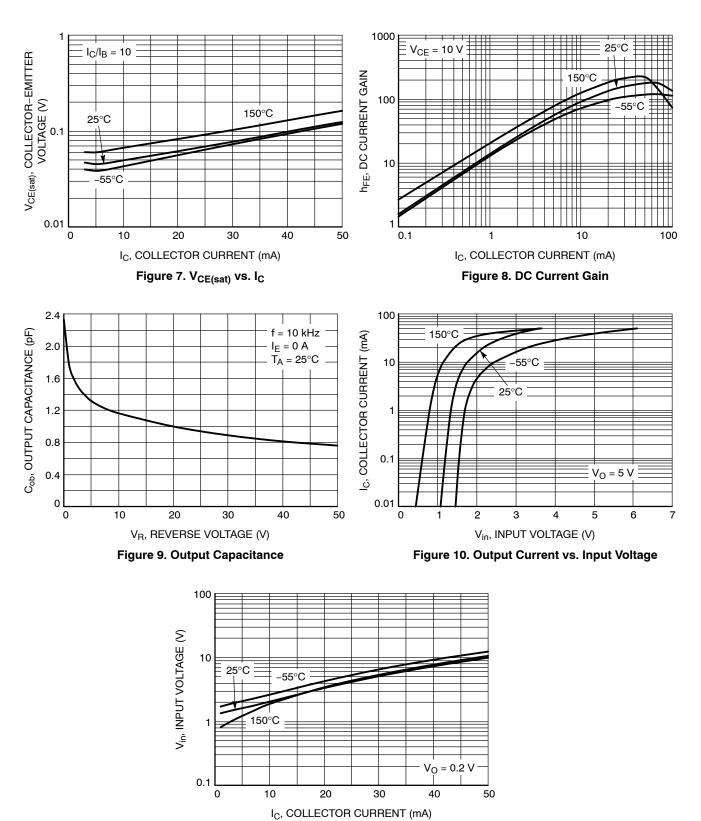
TYPICAL CHARACTERISTICS MUN2211, MMUN2211L, MUN5211, DTC114EE, DTC114EM3









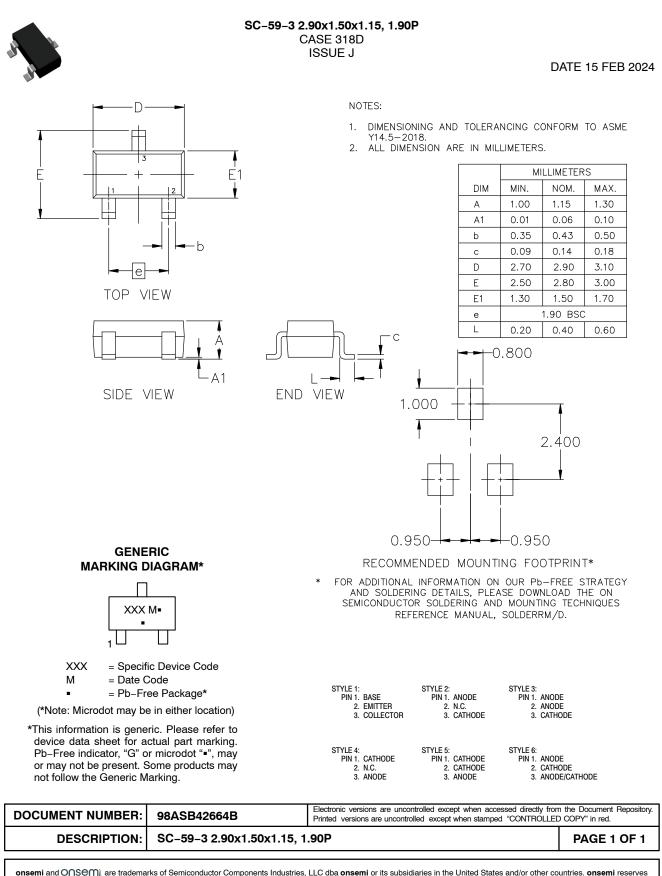


TYPICAL CHARACTERISTICS – NSBC114EF3

Figure 11. Input Voltage vs. Output Current



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SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318**

ISSUE AU

DATE 14 AUG 2024









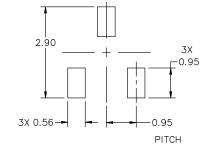




XXX = Specific Device Code М = Date Code

= Pb-Free Package .

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



| MILLIMETERS | | | | | |
|-------------|------|------|------|--|--|
| DIM | MIN | NOM | МАХ | | |
| А | 0.89 | 1.00 | 1.11 | | |
| A1 | 0.01 | 0.06 | 0.10 | | |
| b | 0.37 | 0.44 | 0.50 | | |
| с | 0.08 | 0.14 | 0.20 | | |
| D | 2.80 | 2.90 | 3.04 | | |
| E | 1.20 | 1.30 | 1.40 | | |
| е | 1.78 | 1.90 | 2.04 | | |
| L | 0.30 | 0.43 | 0.55 | | |
| L1 | 0.35 | 0.54 | 0.69 | | |
| Ηe | 2.10 | 2.40 | 2.64 | | |
| Т | 0° | | 10° | | |

NOTES:

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: 1.

2. MILLIMETERS.

MILLIME IERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE 3.

BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS, OR GATE BURRS.

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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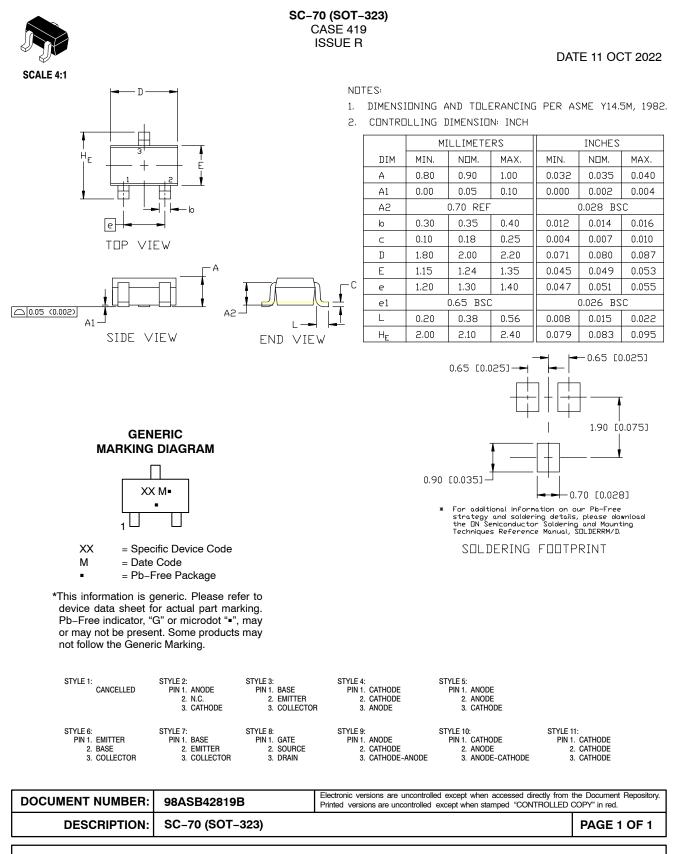
DATE 14 AUG 2024

| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | ı | |
|---|---|---|--|------------------|------------------|
| STYLE 9: | STYLE 10: | STYLE 11: | STYLE 12: | STYLE 13: | STYLE 14: |
| PIN 1. ANODE | PIN 1. DRAIN | PIN 1. ANODE | PIN 1. CATHODE | PIN 1. SOURCE | PIN 1. CATHODE |
| 2. ANODE | 2. SOURCE | 2. CATHODE | 2. CATHODE | 2. DRAIN | 2. GATE |
| 3. CATHODE | 3. GATE | 3. CATHODE-ANODE | 3. ANODE | 3. GATE | 3. ANODE |
| STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: | STYLE 19: | STYLE 20: |
| PIN 1. GATE | PIN 1. ANODE | PIN 1. NO CONNECTION | PIN 1. NO CONNECTION | I PIN 1. CATHODE | PIN 1. CATHODE |
| 2. CATHODE | 2. CATHODE | 2. ANODE | 2. CATHODE | 2. ANODE | 2. ANODE |
| 3. ANODE | 3. CATHODE | 3. CATHODE | 3. ANODE | 3. CATHODE-ANODE | 3. GATE |
| STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: | STYLE 25: | STYLE 26: |
| PIN 1. GATE | PIN 1. RETURN | PIN 1. ANODE | PIN 1. GATE | PIN 1. ANODE | PIN 1. CATHODE |
| 2. SOURCE | 2. OUTPUT | 2. ANODE | 2. DRAIN | 2. CATHODE | 2. ANODE |
| 3. DRAIN | 3. INPUT | 3. CATHODE | 3. SOURCE | 3. GATE | 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE | | | | |

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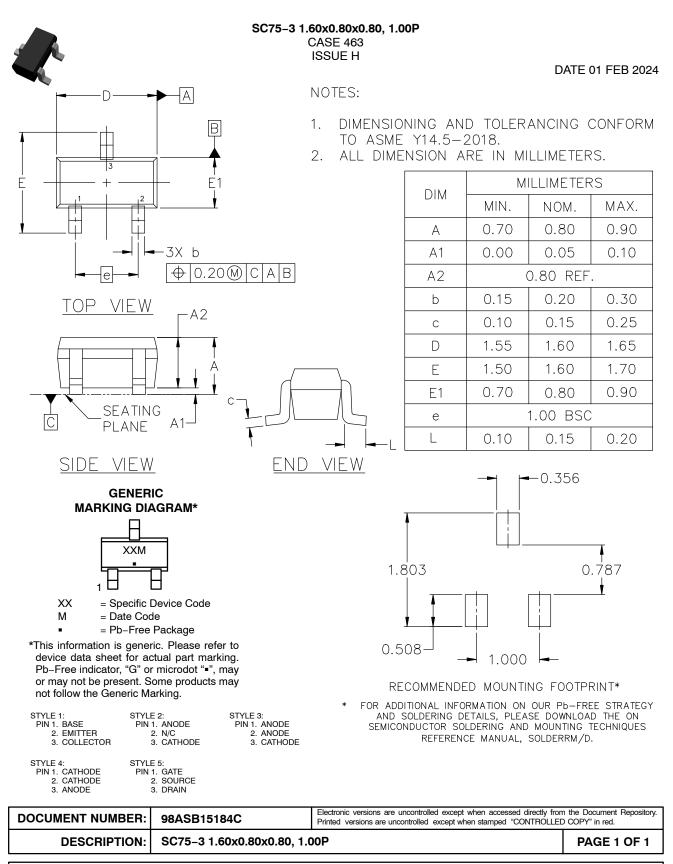
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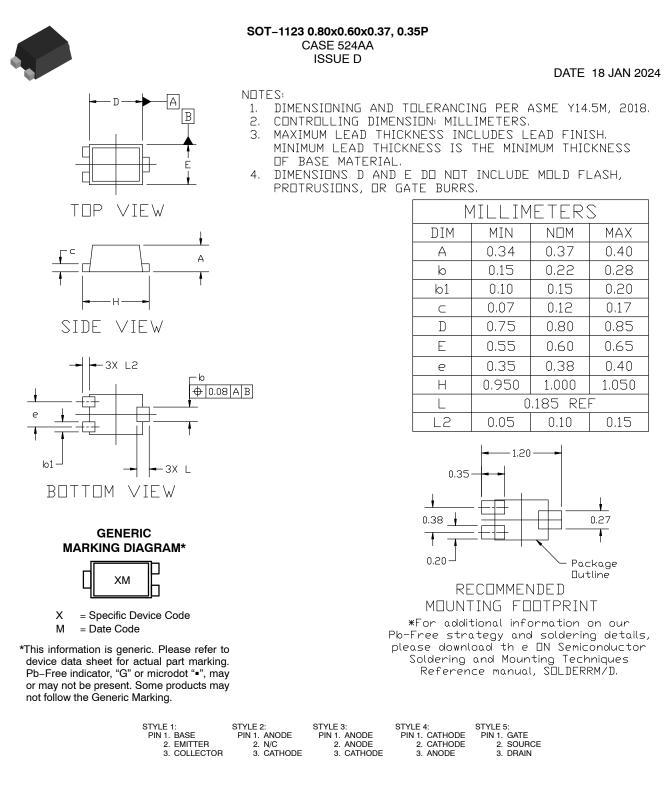
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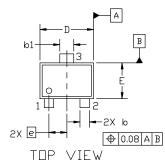


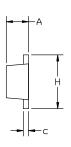
SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

DATE 24 JAN 2024

NDTES:

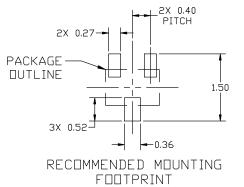
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- 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM З. LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, 4. PROTRUSIONS OR GATE BURRS.



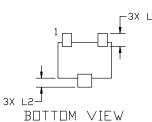


SIDE VIEW

| | | MILLIMETERS | | | |
|---|-----|-------------|----------|------|--|
| | DIM | MIN. | NDM. | MAX. | |
| 1 | А | 0.45 | 0.50 | 0.55 | |
| | Ø | 0.15 | 0.21 | 0.27 | |
| | b1 | 0.25 | 0.31 | 0.37 | |
| | С | 0.07 | 0.12 | 0.17 | |
| | D | 1.15 | 1.20 | 1.25 | |
| | E | 0.75 | 0.80 | 0.85 | |
| | e | | 0.40 BSC | | |
| | Н | 1.15 | 1.20 | 1.25 | |
| | L | 0.29 REF | | | |
| | L2 | 0.15 | 0.20 | 0.25 | |



*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.



GENERIC **MARKING DIAGRAM***



XX = Specific Device Code Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

| 2. EMITTER 2. | II: STYLE 3: ANODE PIN 1. ANODE N/C 2. ANODE CATHODE 3. CATHODE | STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN | | |
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